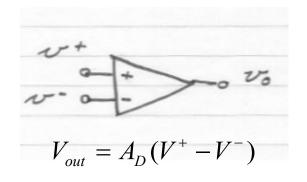
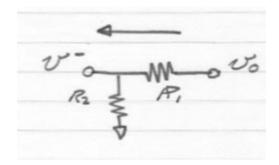
ECE137A, Notes Set 14: Op-Amps

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Operational Amplifier



Characteristics of op-amp: A_d is very large. Very large CMRR Large R_{in} . Small R_{out}

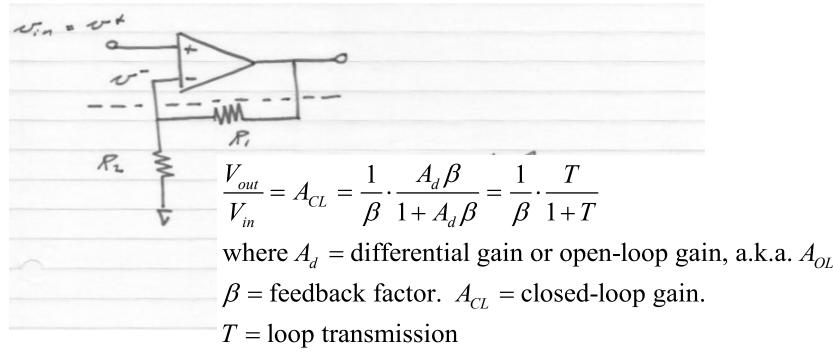


Example of feedback network:

 $V^{-} = \beta V_{out}$ where $\beta = R_2 / (R_1 + R_2)$

Operational Amplifier with Feedback

Combine these:



$$\frac{V_{out}}{V_{in}} = A_{CL} = \begin{cases} 1/\beta \text{ if } T >> 1\\ A_d \text{ if } T << 1 \end{cases}$$

If the loop transmission is very large,

the closed-loop gain is precisely set by the feedback factor

Negative feedback

Feedback can provide precise control of circuit gain.

If $A_d\beta$ is large, then the gain is contolled by the feedback resistors

Note that the external feedback components also set the DC bias.

Op-amp bias is almost always set by the feedback network: For now, analyze by assuming that Vout=0V, and work back to the input to find (V⁺-V⁻).

An op-amp is an amplifier that: is designed for use with feedback operates usually over a range of supply voltages has a very large voltage gain usually (not always) has a large input impedance usually (not always) has a small output impedance is designed to not oscillate when feedback is applied (see ece137B)

Bias analysis of op-amps

There will be a small mismatch between input transistors, and possibly also of their load, etcetera. As a result:

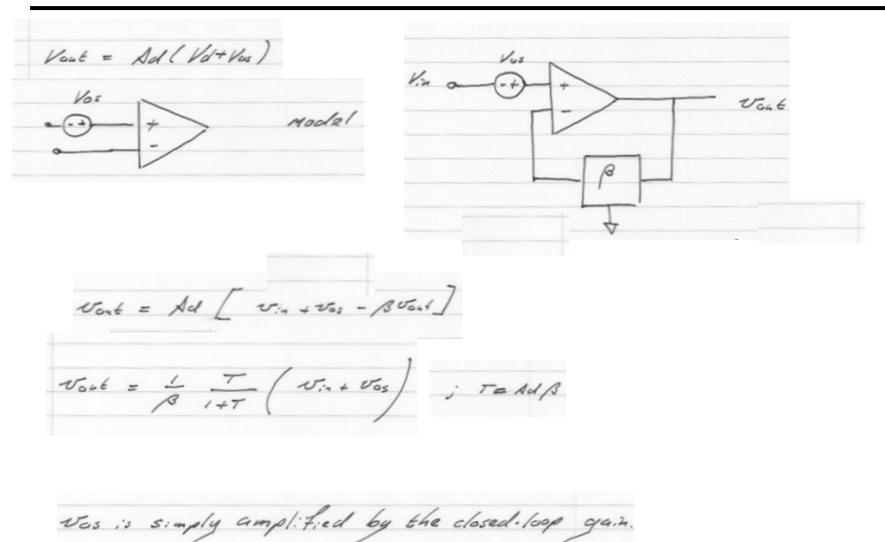
$$V_{out} = A_d (V_d + V_{os}) = A_d (V_{in}^+ - V_{in}^- + V_{os})$$

Vos is called the offset voltage, and might be 0.1-10mV. If $A_d=10^6$ and $V_{os}=1$ mV, then a zero-volt input would force the output to clipping.

Consequently, op-amps are always used with feedback

DC analysis is performed by assuming that V_{out} =0V, and working backward to find the required V_d to obtain this. This value of V_d is the offset voltage V_{os} .

Finding Vout given an offset voltage



How to get high voltage gain ?

We seek $A_D \beta >> 1$, so large op-amp gain is desired.

Suppose $V_{CQ} \ll V_{CC} \rightarrow R_L \cong V_{CC} / I_C$ $-A_V = g_m R_{Leq} = g_m (R_L || R_{CE}) < g_m R_L = (I_C / V_T) (V_{CC} / I_C) = V_{CC} / V_T$ If $V_{CC} = 10$ V, then $||A_V|| < 10$ V/26mV $\cong 400$ \rightarrow gain is limited by the power supply

$$V_{in} = V_{in} = V_{A1} = V_{A2} \quad \text{Then } R_{CE1} = R_{CE2} = V_A / I_C$$

$$V_{out} = V_{out} = g_{m1}R_{Leq} = g_{m1}(R_{CE1} \parallel R_{CE2}) = (I_C / V_T)(V_A / 2I_C) = V_A / 2V_T$$

$$If V_A = 100V, \text{ then } ||A_V|| = 50V/26mV \cong 2000$$

$$\rightarrow \text{ gain is limited by the Early voltage}$$

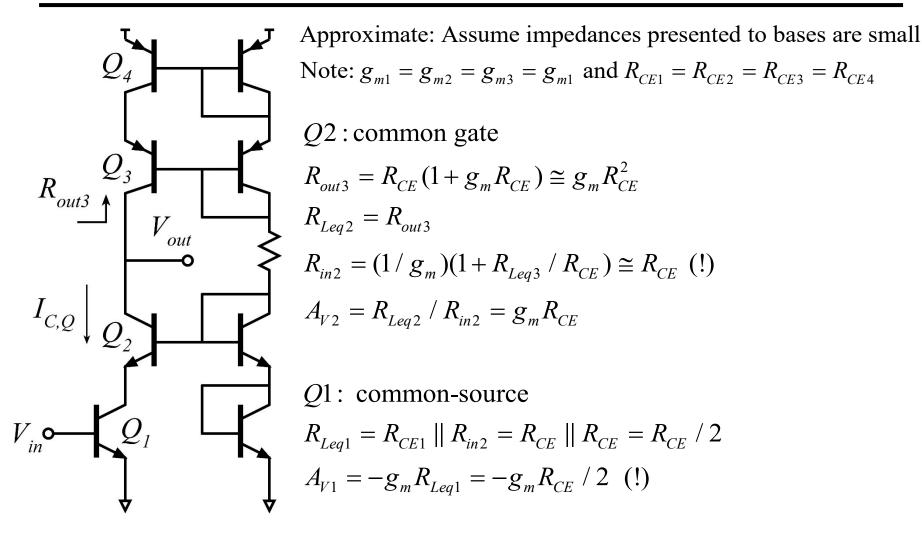
How to get high voltage gain ?

$$\begin{split} V_{DQ} & \bigvee_{DQ} \\ V_{DD} \\ V_{DQ} \\$$

$$V_{in} = \begin{bmatrix} V_{CC} \\ M_2 \\ V_{out} \\ M_1 \\ V_{in} \end{bmatrix}$$

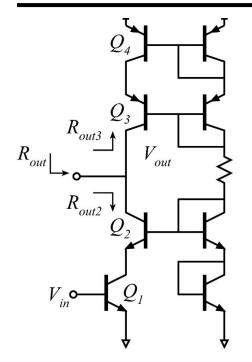
Suppose $\lambda_1 = \lambda_2$ Then $R_{DS1} = R_{DS2} = 1/\lambda I_D$ $-A_V = g_{m1}R_{Leq} = g_{m1}(R_{DS1} || R_{DS2})$; now assume mobility-limited $= (2I_D / (V_{GS} - V_{TH}))(1/2\lambda I_D) = 1/(\lambda (V_{GS} - V_{TH})))$ but only if $(V_{GS} - V_{TH}) > 2V_T$; otherwise $g_m = I_D / nV_T$ If $1/\lambda = 4V$, then $||A_V|| \le 4V/(2 \cdot n \cdot 26mV) \le 4V/52mV \cong 80$ \rightarrow gain is limited by $(1/\lambda)$. Need low $(V_{GS} - V_{TH})$.

Cascodes for high voltage gain



Overall: $A_V = A_{V1}A_{V2} = -(g_m R_{CE})^2 / 2 = -(V_A / V_T)^2 / 2$ If $V_A = 100$ V then $-A_V = (100$ V/26mV) $^2 / 2 \cong (4000)^2 / 2 = 8 \cdot 10^6$

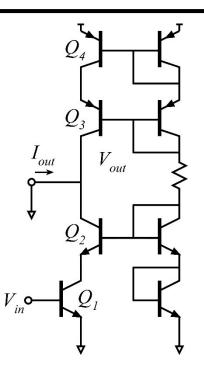
Cascode: alternate analysis



Norton (output) resistance

$$R_{out2} = R_{out3} \cong g_m R_{CE}^2$$
$$R_{out} = R_{out3} \parallel R_{out2} \cong g_m R_{CE}^2 / 2$$

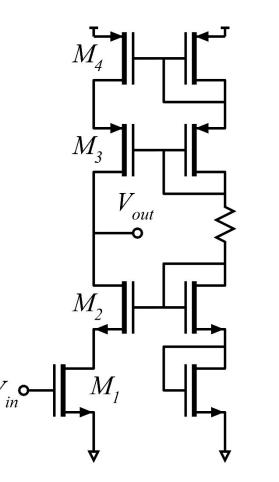




Norton (output) current R_{in2} is now $1/g_m$, so $R_{in2} \ll R_{CE1}$, so $I_{out} \cong g_m V_{in}$

> Norton and Thevenin models: voltage gain is $-(g_m R_{DS})^2/2$

FET Cascode

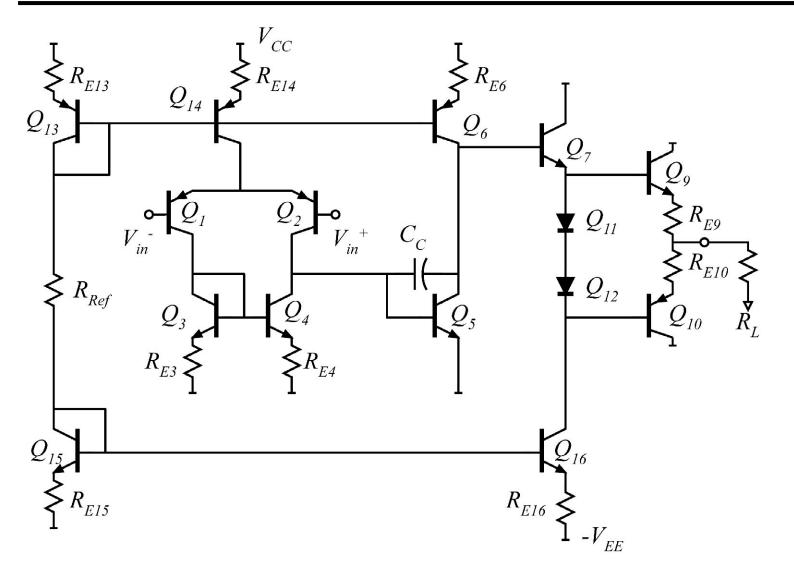


By the same analysis (either method) $A_{V} = A_{V1}A_{V2} = -(g_{m}R_{DS})^{2}/2$

If we assume mobility-limited operation, take $R_{DS} = 1 / \lambda I_D$ and $g_m = 2I_D / (V_{GS} - V_{TH}) < I_D / nV_T$, then $A_{V1}A_{V1} = (2 / \lambda (V_{GS} - V_{TH}))^2 / 2 \le (1 / \lambda n V_T)^2$

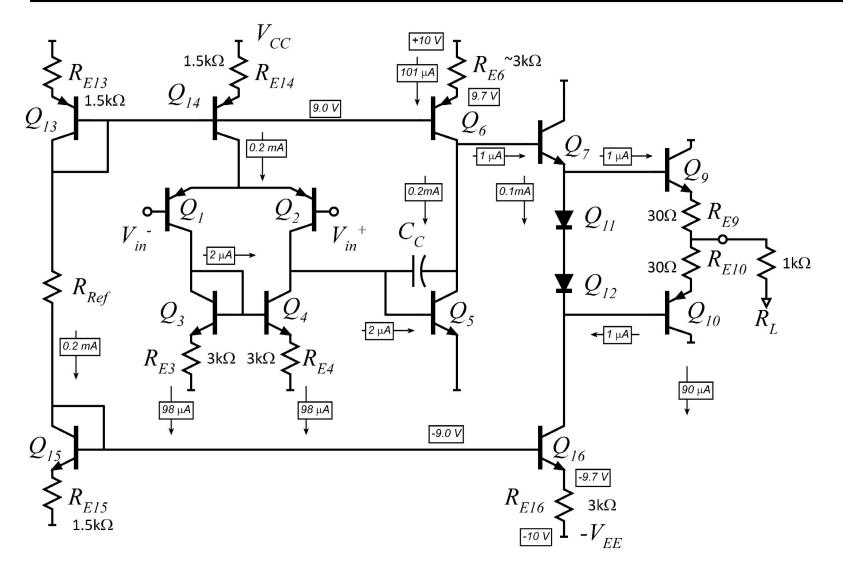
Example: $1/\lambda = 4V$, $(V_{GS} - V_{TH}) = 0.1V \rightarrow |A_{V1}A_{V2}| = 800$

A simple op-amp



The compensation capacitor C_c will be explained in ece137B

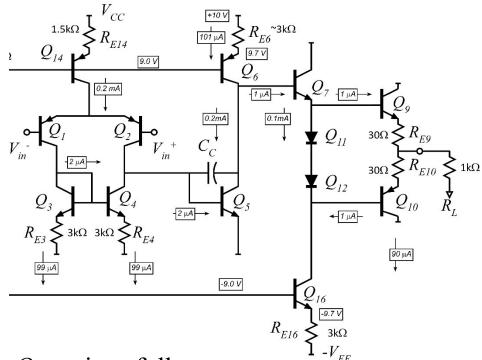
A simple op-amp: DC bias



Assume that all transistors have identical I_s

 $\beta = 100, V_A = 100V$

A simple op-amp: Small-signal (1)

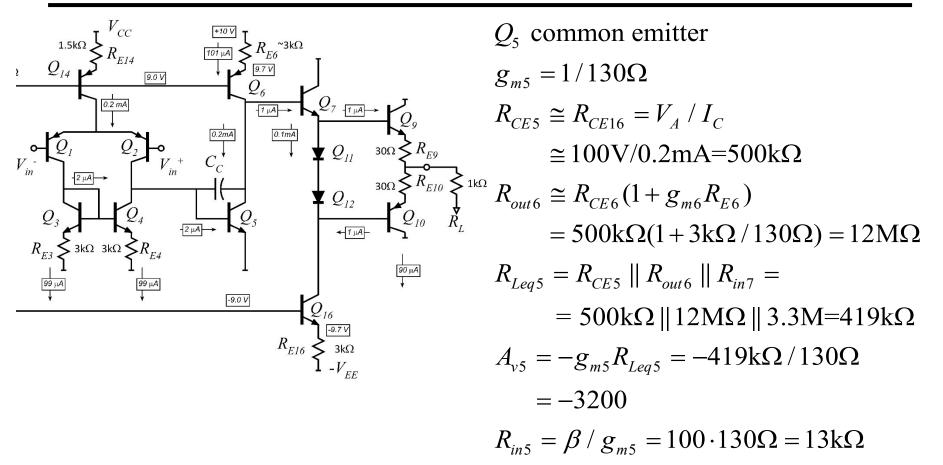


$$Q_9 / Q_{10}$$
: push-pull. Assume Q_9 is on.
Assume $V_{out} = 1V \rightarrow I_{E9} = 1$ mA.
 $g_{m9} = 1/26\Omega$
 $R_{Leq9} \cong 1030\Omega$
 $A_{v9} = R_{Leq9} / (R_{Leq9} + 1/g_m)$
 $= 1000\Omega / (1030\Omega + 26\Omega) = 0.947$
 $R_{in9} = \beta (R_{Leq9} + 1/g_{m9}) = 100 \cdot 1056\Omega$
 $\cong 100$ k Ω

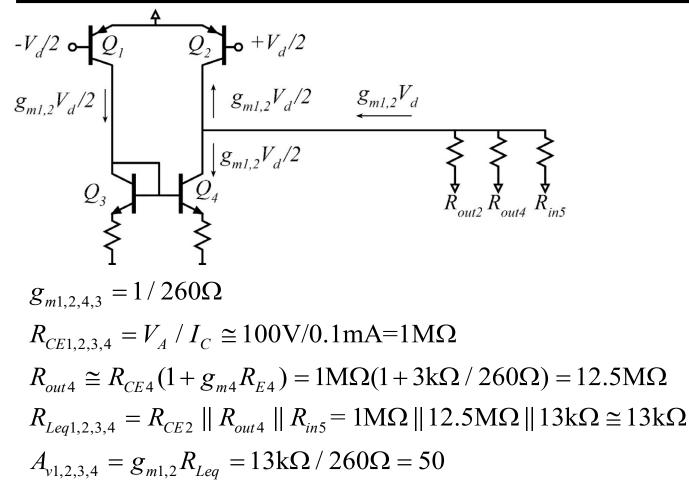
 Q_7 emitter follower.

 $g_{m7} = 1/260\Omega$ $R_{CE7} \cong R_{CE16} = V_A / I_C \cong 100 \text{V}/0.1 \text{mA} = 100 \text{k}\Omega$ $R_{Leq7} = R_{CE7} || R_{CE16} || R_{in9} = 33.3 \text{k}\Omega.$ $A_{v7} = R_{Leq7} / (R_{Leq7} + 1/g_m) = 33.3 \text{k}\Omega / (33.3 \text{k}\Omega + 260\Omega) = 0.992$ $R_{in7} = \beta (R_{Leq7} + 1/g_{m7}) = 100 \cdot 33.6 \text{k}\Omega$ $\cong 3.3 \text{M}\Omega$

A simple op-amp: Small-signal (2)



A simple op-amp: Small-signal (3)



$$R_{in,diff} = 2\beta / g_{m1,2} = 2 \cdot 100 \cdot 260\Omega = 52k\Omega$$

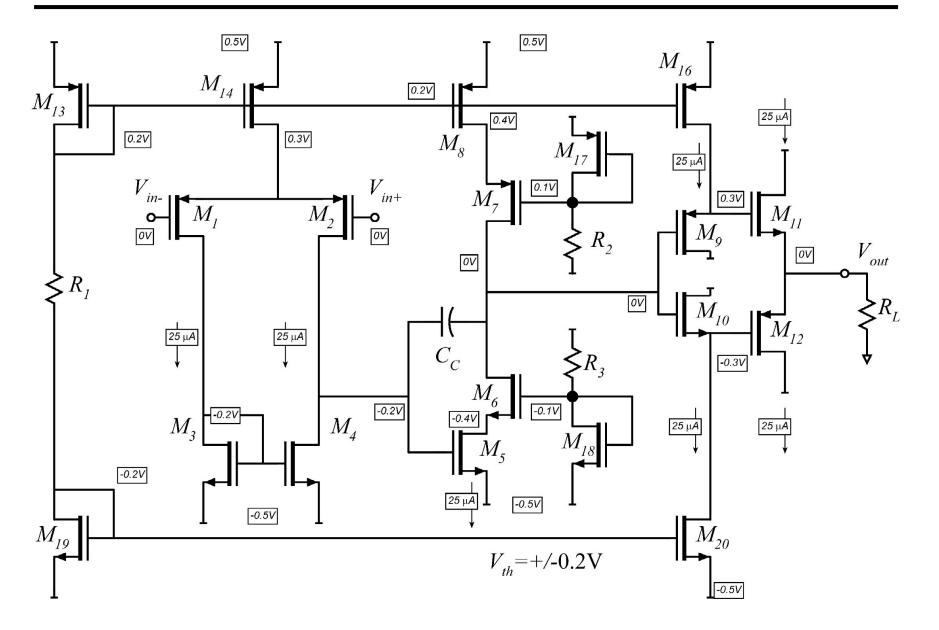
Overall differential gain: $A_d = 50 \cdot 3200 \cdot 0.992 \cdot 0.947 = 150,000$

Common-mode gain (?)

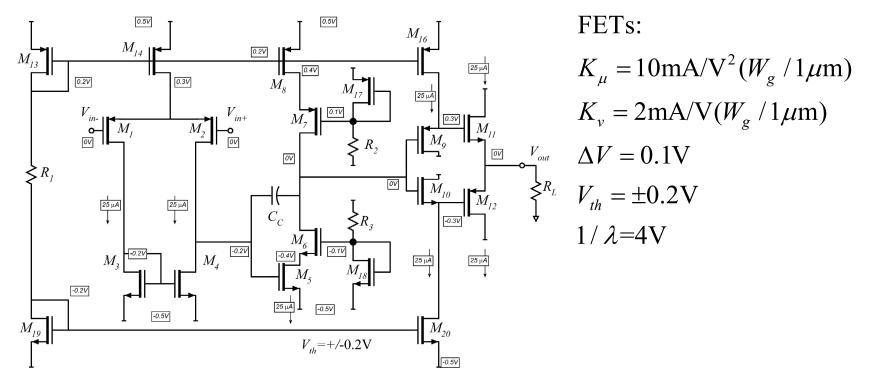
Roch8 SI = Ven/ Post 8 Ven a 0 -Vem SELZ gero as current. SI/2 Rig SI/2

The above andysis suggests intinite CMRR. It needs to be repeated given assumed mismatches between Q1-Q2 and Q3-Q4.

Low-voltage CMOS Amplifier



Low-voltage CMOS Amplifier: Comments

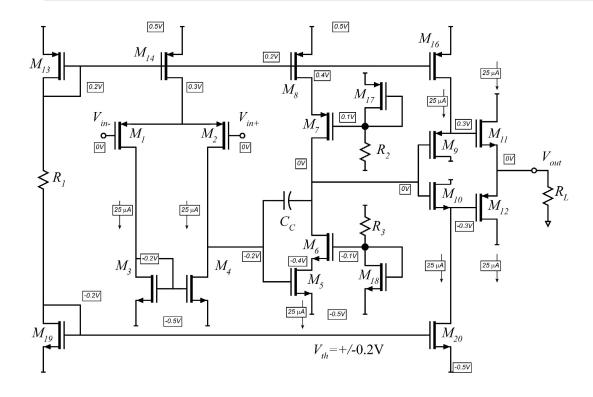


Despite the cascode gain stage and the push-pull output stage,

this design can operate with +/-0.5V supplies and yet provide +/-0.1V output

Most on-wafer CMOS op-amps do not need to drive significant output current and therefore have no source-follower output stage. Much larger voltage swings are then possible.

Low-voltage CMOS Amplifier

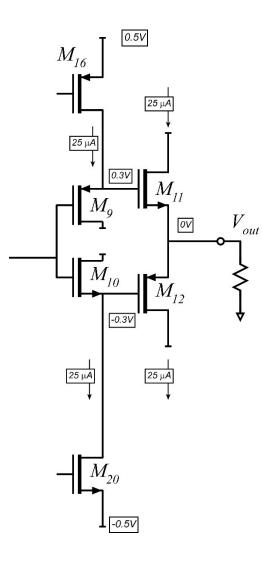


With all FETs except M17,18 operating at $V_{gs} = \pm 0.3$ V and $V_{th} = \pm 0.2$ V, the FET saturation voltage is $V_{DS,sat} = 0.1$ V.

Note carefully that all FETs are biased with $V_{DS} \ge 0.1$ V.

All FET widths can be calculated from $I_D = K_{\mu} (V_{gs} - V_{th})^2 (1 + \lambda V_{DS})$ where $K_{\mu} = 10 \text{mA/V}^2 (W_g / 1 \mu \text{m})$.

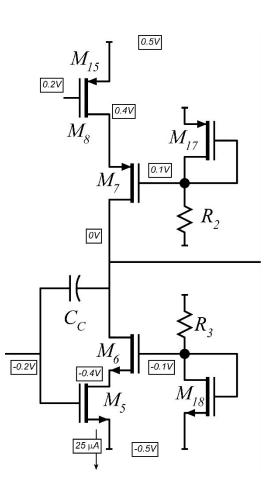
Diamond driver output stage



This is a different form of a push-pull output stage. DC bias design is similar to a current mirror. $V_{gs9} + V_{gs10} = V_{gs11} + V_{gs12}.$ If $I_{D16,9} = I_{D10,20}$, and if $W_{g11}/W_{g9} = W_{g12}/W_{g10}$ then $I_{D11,12} / I_{D9,10,16,20} = W_{g11} / W_{g9}$ For large output signals, M9 and M11 carry the positive swing while M10 and M12 carry the negative swing Voltage gain is calculated in the usual way. Close to 1 if $R_L >> (1 / g_{m11,12})$ M16 and M20 are biased with $|V_{DS}| = 0.2 V$, while $|V_{DS,sat}| = 0.1$ V, so the maximum

output is ± 0.1 V. Not very large.

Cascode gain stage



Using $I_D = K_{\mu} (V_{gs} - V_{th})^2 (1 + \lambda V_{DS})$, pick R_2 and R_3 , and W_{g17} and W_{g18} , so that $V_{gs17} = V_{gs1} = 0.4$ V.

This biases M8 and M5 with $V_{DS} = 0.1$ V.

Given the bias conditions, $V_{DS,sat} = 0.1$ V for M8 and M5.

$$g_{m} = 2I_{D} / (V_{gs} - V_{th}) = 2(25\mu\text{A})/(0.1\text{V}) = 0.5\text{mS}.$$

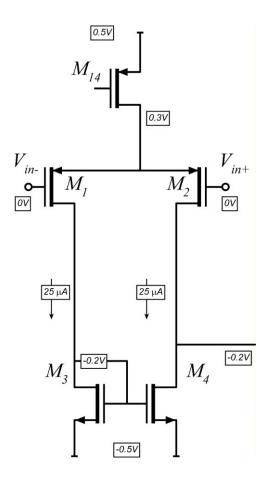
$$R_{DS} = 1 / \lambda I_{D} = 4\text{V}/25\mu\text{A} = 160\text{k}\Omega$$

As derived earlier,

$$A_{v5}A_{v6} = -(g_{m}R_{DS})^{2} / 2 = 3,200$$

For M6 and M7: $V_{DS,sat} = 0.1$ V but $V_{DS,bias} = 0.4$ V. Consequently, the maximum output is ± 0.3 V.

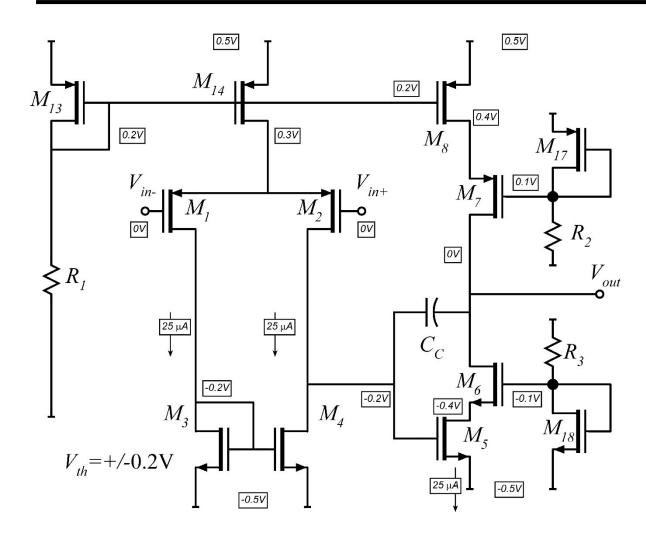
Differential Input stage



 $g_m = 2I_D / (V_{gs} - V_{th}) = 2(25\mu\text{A})/(0.1\text{V}) = 0.5\text{mS}.$ $R_{DS} = 1 / \lambda I_D = 4\text{V}/25\mu\text{A} = 160\text{k}\Omega$ As derived earlier, $A_{v1,2,3,4} = (g_m R_{DS}) / 2 = 40$

Overall op-amp gain: $A_D = A_{v1,2,3,4} A_{V5} A_{V6} A_{V9} A_{V11} \cong 40 \cdot 3200 = 128,000$

Op-amp with no output buffer



If the load impedances are always very high, then we can remove the output buffer

The outuput can then swing ± 0.3 V

More on op-amp design

Please see the documents associated with lab project 3